

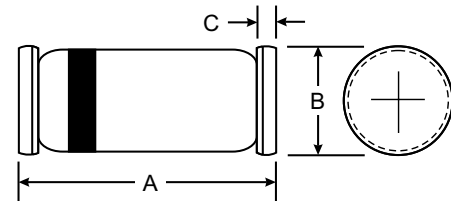


Features

- Silicon epitaxial planar diode
- High speed switching diode
- 500 mW power dissipation

Mechanical Data

- Case: SOD-80/LL34, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)



| LL34/ SOD-80 | | |
|----------------------|------|------|
| Dim | Min | Max |
| A | 3.30 | 3.70 |
| B | 1.30 | 1.60 |
| C | 0.28 | 0.50 |
| All Dimensions in mm | | |

Maximum Ratings @ T_A = 25°C unless otherwise specified

| Characteristic | Symbol | BAV100 | BAV101 | BAV102 | BAV103 | Unit |
|--|-------------------|-------------------|--------|--------|--------|------|
| Reverse voltage | V _R | 50 | 100 | 150 | 200 | V |
| Repetitive peak reverse voltage | V _{RRM} | 60 | 120 | 200 | 250 | V |
| Forward current | I _(AV) | 0.25 | | | | A |
| Forward surge current t _p =1s | I _{FSM} | 1.0 | | | | A |
| Power dissipation | P _V | 500 | | | | mW |
| Thermal resistance junction to ambient | R _{θJA} | 500 ¹⁾ | | | | K/W |
| Thermal resistance junction to lead | R _{θJL} | 350 | | | | K/W |
| Junction temperature | T _j | 175 | | | | |
| Storage temperature range | T _{STG} | - 65 --- + 175 | | | | |

¹⁾ Device mounted on PC board 50mm×50mm×1.6mm .



FIG 1. REVERSE CURRENT VS. JUNCTION TEMPERATURE

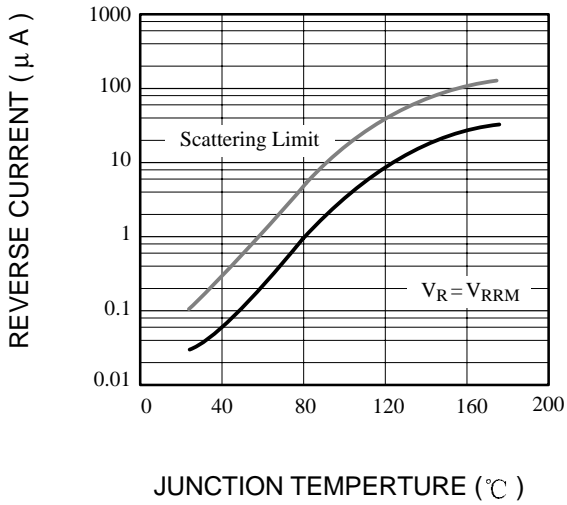


FIG 2. FORWARD CURRENT VS. FORWARD VOLTAGE

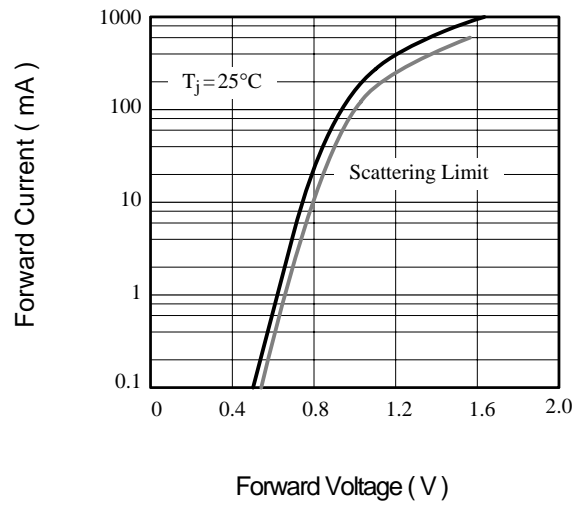


FIG 3. DIFFERENTIAL FORWARD RESISTANCE VS. FORWARD CURRENT

